

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: YOSHIDA et al.  
 Serial No.: 09/416,959  
 Filed: October 13, 1999  
 For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE  
 AND PROCESS FOR MANUFACTURING THE SAME  
 Group: 2812  
 Examiner: J. Hack

SECOND SUPPLEMENTAL PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
 Washington, D.C. 20231

September 5, 2000

Sir:

In supplement to the amendments filed on October 13, 1999  
 and January 20, 2000, please amend the above-identified  
 application as follows:

IN THE CLAIMS

Please amend claims 1 and 2 as follows:

1. (Amended) A process for manufacturing a semiconductor  
 integrated circuit device, comprising the steps of:
- (a) forming a first wiring layer over a main surface  
 of a semiconductor substrate;
  - (b) forming a first insulating film on the first  
 wiring layer;
  - (c) forming a second wiring layer which is comprised  
 of first conductor film and a first film formed over the first  
 conductor film over the first insulating film;

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